

Si Zener-diode Chip – TK0S06ZDN

1. Scope

- The specification applies to planar Zener diode.
- Extra lower leakage current
- Special thickness for special assembly process.

2. Structure

- Planar type Zener diode.
- Electrode P (anode) : Aluminum. (Gold for option)
- Electrode N (cathode) side : Gold.

3. Size

- Chip size : 6.5mil × 6.5mil ± 0.8mil (0.1651mm × 0.1651mm ± 0.020mm)
- Thickness : 4.0mil ± 0.6mil (0.110mm ± 0.015mm)
- Pad Size : 4.8mil × 4.8mil ± 0.4mil (0.122mm × 0.122mm ± 0.010mm)
- Pattern drawing : per fig. 1

4. Electrical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	Rank A: I _F = 10mA	3		5	V
		Rank B: I _F = 10mA	5		7	V
		Rank C: I _F = 10mA	6		8	V
Forward Leakage current	I _F	Rank A: V _F = 2.5V			500	nA
		Rank B: V _F = 4V			500	nA
		Rank C: V _F = 5V			500	nA
Reverse Voltage	V _Z	Rank A: I _R = 10mA	3.5		6	V
		Rank B: I _R = 10mA	8		13	V
		Rank C: I _R = 10mA	8		13	V
Reverse Leakage current	I _R	Rank A: V _R = 3V			500	nA
		Rank B: V _R = 4V			500	nA
		Rank C: V _R = 5V			500	nA

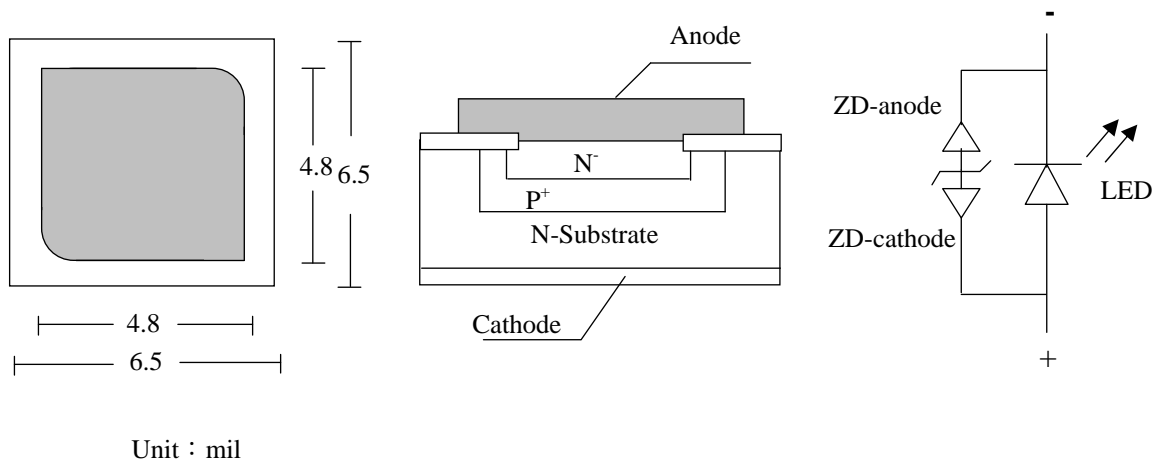


fig. 1

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